

## isc Silicon NPN Power Transistors

## MJD31C

### DESCRIPTION

- DC Current Gain  $-h_{FE} = 25$ (Min)@  $I_C = 1A$
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)\ CEO} = 100V$ (Min)
- Complement to Type MJD32C
- DPAK for Surface Mount Applications
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

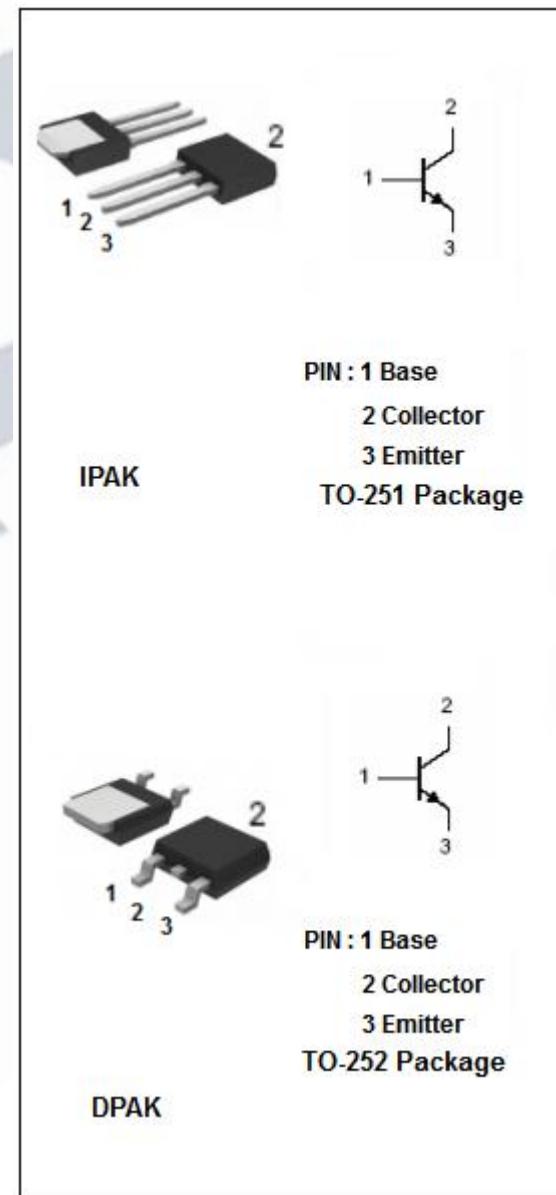
- Designed for use in general purpose amplifier and low speed switching applications.

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	3	A
$I_{CM}$	Collector Current-Pulse	5	A
$I_B$	Base Current	1	A
$P_c$	Collector Power Dissipation $T_c=25^\circ C$	15	W
	Collector Power Dissipation $T_a=25^\circ C$	1.56	
$T_j$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ C$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	8.3	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	80	$^\circ C/W$



**isc Silicon NPN Power Transistors****MJD31C****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(\text{BR})\text{CEO}}$	Collector-Emitter Breakdown Voltage	$I_C= 30\text{mA}; I_B= 0$	100		V
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C= 3\text{A}; I_B= 0.375\text{A}$		1.2	V
$V_{\text{BE}(\text{on})}$	Base-Emitter On Voltage	$I_C= 3\text{A}; V_{\text{CE}}= 4\text{V}$		1.8	V
$I_{\text{CES}}$	Collector Cutoff Current	$V_{\text{CE}}= 100\text{V}; V_{\text{EB}}= 0$		20	$\mu\text{A}$
$I_{\text{CEO}}$	Collector Cutoff Current	$V_{\text{CE}}= 60\text{V}; I_B= 0$		50	$\mu\text{A}$
$I_{\text{EBO}}$	Emitter Cutoff Current	$V_{\text{EB}}= 5\text{V}; I_C= 0$		1.0	mA
$h_{\text{FE}-1}$	DC Current Gain	$I_C= 1\text{A}; V_{\text{CE}}= 4\text{V}$	25		
$h_{\text{FE}-2}$	DC Current Gain	$I_C= 3\text{A}; V_{\text{CE}}= 4\text{V}$	10	50	
$f_T$	Current-Gain—Bandwidth Product	$I_C= 0.5\text{A}; V_{\text{CE}}= 10\text{V}$	3		MHz

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## Outline Drawing

